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Controlling the nanomorphology of thin conformal Cu₂S overlayers grown on Cu₂O compact layers and nanowires

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Abstract

Thin conformal Cu₂S overlayers are grown on Cu₂O compact layers (CLs) and nanowires (NWs) by ion exchange reaction (IER). This method is based on the exchange of O^{2-} into S^{2-} ions at the surface of Cu₂O in a solution-containing Na₂S acting as the sulphur ions source. The Cu₂S overlayers are grown under different experimental conditions by varying the Na₂S concentration and the duration of the IER process, thus leading to different Cu₂S nanomorphologies. In particular, when a concentration of 2 mM Na₂S is used, hexagonal Cu₂S nanocrystals are formed on the surface of both Cu₂O CLs and NWs. These nanocrystals are of larger size at the ridges of the Cu₂O cubes in CLs and at the tips of Cu₂O in NWs. The high-quality crystal structure and composition of Cu₂S are confirmed by high resolution transmission electron spectroscopy and X-ray photoluminescence spectroscopy.

Keywords: Ion exchange reaction; nanomorphology; overlayer; copper oxide; copper sulfide.

1. Introduction

Nanostructured metal chalcogenides are attracting considerable attention due to their exceptional physical and chemical properties [1, 2]. Applications of these materials are as diverse as thermoelectrical systems, memories, energy conversion, and energy storage devices [3]. Cu_2S is a typical metal chalcogenide behaves is a p-type semiconductor with an indirect band gap E_g =1.2 eV. Depending on the preparation method, Cu_2S thin films can adopt variety morphologies such as nanowires [4], nanocages [5] or nanoparticles with different geometries [6]. Nanostructured Cu_2S is

used in lithium ion batteries [7], quantum dots solar cells as counter-electrodes [8] or photovoltaic devices [9]. Cu_2S can be prepared by atomic layer deposition [10], physical vapor deposition [11] or hydrothermal [12], among others.

Together with several other metal oxides [13-15] cuprous oxide Cu₂O is a promising material for photoelectrochemical (PEC) solar energy conversion [16]. In this work we report the preparation and nanomorphology of thin conformal Cu₂S overlayers grown on Cu₂O compact layers (CLs) and nanowires (NWs). The Cu₂S overlayers are grown via an ion exchange reaction (IER) consisting in the exchange of oxygen ions from Cu₂O with sulfur ions from Na₂S contained in an aqueous solution. The nanomorphology of the Cu₂S overlayers can be precisely controlled by adjusting the Na₂S concentration and the IER reaction time, and is independent of the starting Cu₂O morphology, either CLs or NWs.

2. Materials and methods

Cu₂O nanostructures are fabricated as CLs by electrodeposition (see Electronic Supplementary Material ESM†, Section 1.1) and as NWs by anodization (ESM† Section 1.2). Then Cu₂O CLs and NWs (Fig. S1) are used for growing Cu₂S overlayers by IER. Different Cu₂O samples are immersed in 2 mM and 5 mM Na₂S solutions during different times at 80 °C (ESM†, Section 1.3). All materials are analyzed by scanning electron microscopy (SEM, Jeol JSM-6700F) and high-resolution transmission electron microscopy (HR-TEM, JEM-2010). The HR-TEM analysis is carried out on the samples in powder form. Absolute ethanol is added to the powder in a 10 ml bottle and deposited three drops at intervals of 5 minutes on copper grids. X-ray photoelectron spectroscopy (XPS) was performed under monochromatic Al K α radiation (hv=1486.7 eV) was used at 300 W, 14 kV under ultra-high vacuum.

3. Results and discussion

3.1 Morphology of the Cu₂S overlayers

When carried out during 15 minutes in a 2 mM solution, the IER growth of Cu₂S is slow (Fig 1a,b). It induces the formation of a homogeneous layer of nanostructured Cu₂S crystals all over the surface of the Cu₂O CLs (Fig. 1a). The Cu₂S nanocrystals grow preferentially on the ridges of the cubic Cu₂O structures (Fig. 1b,c). These crystals are of larger size than those growing on the faces of the Cu₂O cubes (Fig. 1d). As expected the Cu₂S nanocrystals are hexagonal in shape. A longer IER duration time up to 60 minutes does not affect drastically the morphology of the Cu₂S overlayer (Fig. 1e), although a thickening of the Cu₂S crystals on the ridges progressively takes place due to an

increasing overlap of the crystals (Fig. 1f). Besides, when the Na₂S concentration is increased up to 5 mM, the Cu₂S growth kinetics is faster and takes place in only 2 minutes (Fig. 1g). The Cu₂S overlayer is also very homogeneous, although there are no nanostructures formed on the surface (Fig. 1h,i). A perpendicular cross-arrangement of the constitutive Cu₂S nanocrystals is clearly observed that is similar to that observed in a 2 mM Na₂S solution after 15 minutes (Fig. 1d). Finally, when Cu₂O is immersed in a 2 mM solution, adhesion of the Cu₂S overlayer on Cu₂O CLs is excellent, thus making potential applications realistic. However, we note that adhesion of the Cu₂S overlayer is reduced when using a higher Na₂S concentration of 5 mM, thus leading to partial detachment of the Cu₂S overlayer.

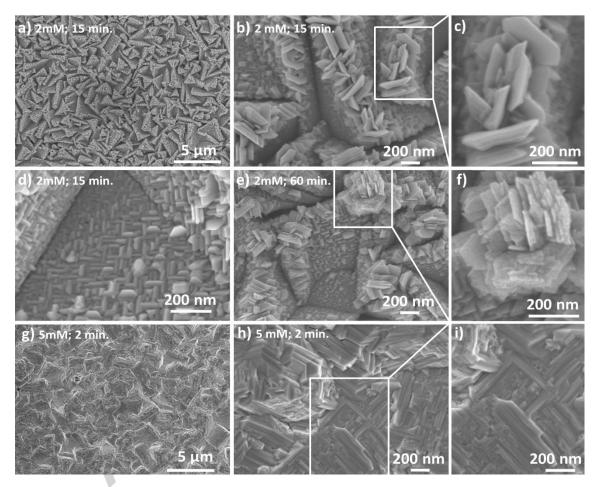


Fig. 1 SEM micrographs of Cu₂O compact layers (CLs) coated with a Cu₂S overlayer prepared by IER under different Na₂S concentrations and reaction times. Magnifications of the Cu₂S nanocrystals inside the white squares are shown on the right images.

IER has been also conducted on Cu_2O NWs in solutions containing Na_2S concentrations of respectively 2 mM and 5 mM. After 30 minutes of IER in a 2 mM solution an overlayer of Cu_2S nanocrystals grows around the NWs (Fig. 2a). The morphology of the Cu_2S layer (Fig. 2b) is comparable to that obtained in similar conditions on CLs (Fig. 1b,e). Noticeably, larger Cu_2S

nanostructures grow on the Cu₂O NWs tips, a phenomenon which is reminiscent of the higher concentration of Cu₂S nanocrystals on the Cu₂O CLs ridges (*vide supra*). On the other hand, when the IER process is carried out in a 5 mM solution, the Cu₂S overlayer is not nanostructured (Fig. 2c) although the Cu₂S crystal structure formed after 5 minutes is still visible (Fig. 2d). This morphology resembles that of the Cu₂S-coated Cu₂O CLs grown into a 5 mM solution (see Fig. 1h,i). However, in contrast to Cu₂S overlayers grown on CLs using a 5 mM Na₂S concentration, the Cu₂S overlayers grown on NWs in 5 mM solutions exhibit a very good adhesion to Cu₂O.

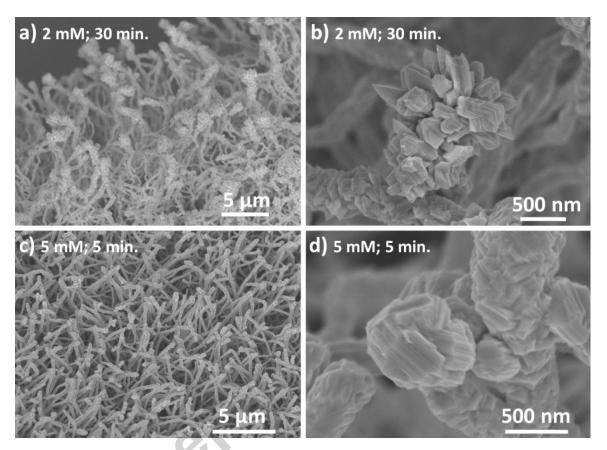


Fig. 2 SEM micrographs of Cu₂O nanowires (NWs) coated by a Cu₂S overlayer prepared an IER process under different Na₂S concentrations and reaction times.

3.2 High resolution transmission electron microscopy (HR-TEM)

Images in Fig. 3a,b correspond to Cu₂S-coated Cu₂O samples for respectively a CLs and NWs. In both images dark and bright areas are observed. The selected regions delimited by white squares are analysed by fast Fourier transform (FFT). Fig. 3c represents the FFT performed in the selected region of the brighter area of a CL. It reveals lattice spacing of 3.19, 2.78 and 1.96 Å which can be attributed to the (111), (200) and (220) planes of Cu₂S. In the FFT of the selected region in darker area (Fig. 3d), three lattice spacing of 2.45, 2.13 and 1.50 Å are observed that can be attributed respectively to the crystallographic planes (111), (200) and (220) of Cu₂O. The FFT analysis of the bright selected area of

the NWs (Fig. 3e) reveals an interplanar distance of 1.96 Å corresponding to the (220) plane of Cu_2S . It also unveils the (200) plane corresponding to Cu_2O with a interplanar distance of 2.13 Å. The crystallographic planes of Cu_2O are also observed very clearly in the FFT of the region in the darker area (Fig. 3f).

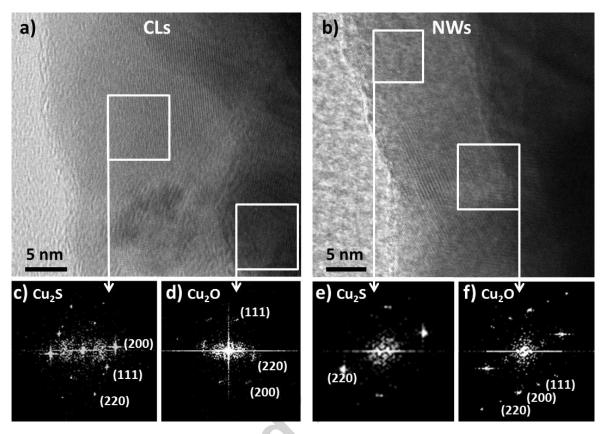


Fig. 3 HR-TEM images of Cu_2S -coated Cu_2O a) CLs and b) NWs. c,d,e,f) FFT analysis of the selected regions in either dark or bright contrast (white squares)

3.3 X-ray photoluminescence spectroscopy (XPS)

We performed X-ray photoelectron spectroscopy (XPS) in order to confirm the formation of Cu_2S (Fig. 4). In the wide XPS spectra are shown the Cu 2p, Cu LMM, O 1s, C 1s and S2p for both CLs and NWs (Fig. 4a,b). We can observe the Cu $2p_{1/2}$ peak at 952.5 eV and the Cu $2p_{3/2}$ peak at 932.6 eV (Fig. 4c) showing that the oxidation state of copper species correspond to Cu⁺. We have seen no satellite peaks of Cu $2p_{1/2}$ and Cu $2p_{3/2}$ which is an evidence of the absence of Cu²⁺ oxidation state on the surface of the overlayers on CLs and NWs. For both CLs and NWs the S 2p regions (Fig. 4d) show the characteristic shape of an S²⁻ band. Peaks at 162.9 eV and 161.8 eV can be attributed to the S $2p_{1/2}$ and S $2p_{3/2}$ spin-orbit doublet.

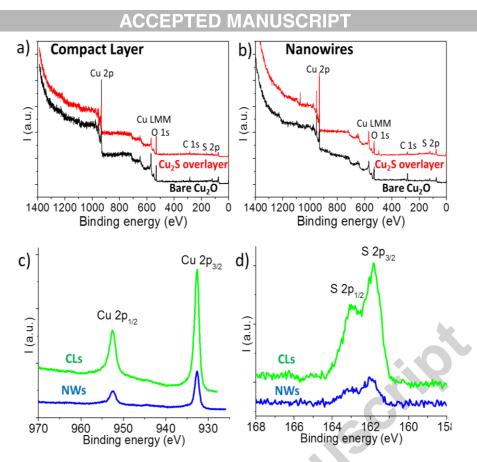


Fig. 4 a,b) Wide scan XPS spectra of Cu₂O CLs and NWs with (red) and without (black) Cu₂S overlayers. c,d) XPS spectra of the Cu₂p and S2p regions of the Cu₂S overlayers on CLs (green) and NWs (blue).

4. Conclusion

The influence of the concentration of Na₂S solution is a critical parameter for the growth of the Cu₂S overlayers on Cu₂O compact layers and nanowires by ion exchange reaction. When a concentration of 2 mM Na₂S is used, hexagonal Cu₂S nanocrystals are formed on the surface of both Cu₂O CLs and NWs. The sizes of the crystals are bigger at the ridges of the Cu₂O cubes in CLs and the tips of Cu₂O in NWs. The time scale of the IER process does not affect much the Cu₂S morphology although larger clusters of Cu₂S nanocrystals are formed at the ridges of the CLs. HR-TEM confirms the formation of the Cu₂S single crystals while XPS reveals the high-quality chemical composition of the overlayers. We are presently using these conformal Cu₂S overlayers to protect Cu₂O electrodes during photoelectrochemical experiments that will be reported elsewhere [17].

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References

[1] Gao M-R, Jiang J, Yu S-H. Solution-Based Synthesis and Design of Late Transition Metal Chalcogenide Materials for Oxygen Reduction Reaction. Small 2012;8:13-27.

[2] Osterloh FE. Inorganic nanostructures for photoelectrochemical and photocatalytic water splitting. Chem Soc Rev 2013;42:2294-320.

[3] Gao M-R, Xu Y-F, Jiang J, Yu S-H. Nanostructured metal chalcogenides: synthesis, modification, and applications in energy conversion and storage devices. Chem Soc Rev 2013;42:2986-3017.

[4] Liu ZP, Xu D, Liang JB, Shen JM, Zhang SY, Qian YT. Growth of Cu_2S ultrathin nanowires in a binary surfactant solvent. J Phys Chem B 2005;109:10699-704.

[5] Kuo CH, Chu YT, Song YF, Huang MH. Cu₂O Nanocrystal-Templated Growth of Cu₂S Nanocages with Encapsulated Au Nanoparticles and In-Situ Transmission X-ray Microscopy Study. Adv Funct Mater 2011;21:792-7.

[6] Li W, Shavel A, Guzman R, Rubio-Garcia J, Flox C, Fan JD, Cadavid D, Ibanez M, Arbiol J, Morante JR, Cabot A . Morphology evolution of Cu_{2-x}S nanoparticles: from spheres to dodecahedrons. Chem Commun 2011;47:10332-4.

[7] Lai CH, Huang KW, Cheng JH, Lee CY, Hwang BJ, Chen LJ. Direct growth of high-rate capability and high capacity copper sulfide nanowire array cathodes for lithium-ion batteries. J Mater Chem 2010;20:6638-45.

[8] Peng Z, Liu Y, Zhao Y, Chen K, Cheng Y, Chen W. Incorporation of the TiO₂ nanowire arrays photoanode and Cu₂S nanorod arrays counter electrode on the photovoltaic performance of quantum dot sensitized solar cells. Electrochim Acta 2014;135:276-83.

[9] Riha SC, Jin S, Baryshev SV, Thimsen E, Wiederrecht GP, Martinson ABF. Stabilizing Cu₂S for Photovoltaics One Atomic Layer at a Time. ACS Appl Mater Interf 2013;5:10302-9.

[10] Martinson ABF, Riha SC, Thimsen E, Elam JW, Pellin MJ. Structural, optical, and electronic stability of copper sulfide thin films grown by atomic layer deposition. Energ Environ Sci 2013;6:1868-78.

[11] Siol S, Sträter H, Brüggemann R, Brötz J, Bauer GH, Klein A, et al. PVD of copper sulfide (Cu₂S) for PIN-structured solar cells. J Phys D Appl Phys 2013;46:495112.

[12] Yu X, An X. Controllable hydrothermal synthesis of Cu₂S nanowires on the copper substrate.Mater Lett 2010;64:252-4.

[13] Qi H, Wolfe J, Wang D, Fan HJ, Fichou D, Chen Z. Triple-layered nanostructured WO_3 photoanodes with enhanced photocurrent generation and superior stability for photoelectrochemical solar energy conversion. Nanoscale 2014;6:13457-62.

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[14] Fichou D, Pouliquen J, Kossanyi J, Jakani M, Campet G, Claverie J. Extension of the photoresponse of semiconducting zinc-oxide electrodes by 3d impurities absorbing in the visible region of the solar spectrum. J Electroanal Chem 1985;188:167-87.

[15] Jakani M, Campet G, Claverie J, Fichou D, Pouliquen J, Kossanyi J. Photoelectrochemical properties of zinc oxide doped with 3d elements. J Solid State Chem 1985;56:269-77

[16] Paracchino A, Mathews N, Hisatomi T, Stefik M, Tilley SD, Grätzel M. Ultrathin films on copper(I) oxide water splitting photocathodes: a study on performance and stability. Energ Environ Sci 2012;5:8673-81.

[17] Minguez-Bacho I, Courté M, Fan HJ and Fichou D. Conformal Cu₂S-coated Cu₂O nanostructures grown by ion exchange reaction and their photoelectrochemical properties Nanotechnology 2015;26:185401.

Highlights

- Conformal layers of Cu₂S on Cu₂O are grown by ion exchange reaction.

- The morphology of the Cu₂S overlayers is not dictated by the morphology of the starting Cu₂O material.

- Different Cu₂S nanomorphologies are studied by SEM, HRTEM and XPS.

Accepted

- Cu₂S overlayers have a potential application as protection against photodecomposition of Cu₂O photoelectrodes.